



650V TRENCHSTOP™5

Introducing a Technology to Match Tomorrow's High Efficiency Demands



The new TRENCHSTOP™5 IGBT technology from Infineon redefines the “Best-in-Class IGBT” by providing unmatched performance in terms of efficiency. When high efficiency, lower system costs and increased reliability are demanded, TRENCHSTOP™5 is the only option. The new TRENCHSTOP™5 IGBTs deliver a dramatic reduction in switching and conduction losses – for example in application measurement 1.7 efficiency improvement – whilst also offering a 650V breakthrough voltage. Can you afford to wait for the competition to catch up?

Key features and benefits of the brand new 650V TRENCHSTOP™5 IGBT technology

- New benchmark in terms of Best-in-Class efficiency
- Lowest ever switching losses
- $V_{CE(sat)}$ more than 10% lower than previous generation
- 650V breakthrough voltage
- Temperature stable V_f value of Infineon's free-wheeling Rapid diode
- 2.5 factor lower Q_g compared to HighSpeed 3



For further information please visit our website:
www.infineon.com/trenchstop5

